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To: Commissioner of Patents and Trademarks  
Washington, D.C. 20231

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TO 2830 MAIL ROOM  
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Subject:	Serial No. 09/945,436 09/04/01
	Jin-Yuan Lee, Mou-Shiung Lin
	A METHOD FOR MAKING HIGH-PERFORMANCE RF INTEGRATED CIRCUITS
	Grp. Art Unit: 2832

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

U.S. Patent 6,046,101 to Dass et al., "Passivation Technology Combining Improved Adhesion in Passivation and a Scribe Street Without Passivation", discloses a process where passivation is not formed over some scribe streets.

U.S. Patent 5,904,546 to Wood et al., "Method and Apparatus for Dicing Semiconductor Wafers," discloses a dicing process on scribe lines to form planar inductors.

U.S. Patent 6,043,109 to Yang et al., "Method of Fabricating Wafer-Level Package," discloses a IC process (including inductors) where wafers are sawed on scribe lines.

U.S. Patent 5,387,551 to Mizoguchi et al., "Method of Manufacturing Flat Inductance Element," discloses an inductor process and dicing process.

Sincerely,



Stephen B. Ackerman,  
Reg. No. 37761